1S1553~1S1555

Silicon Epitaxial Planar Type

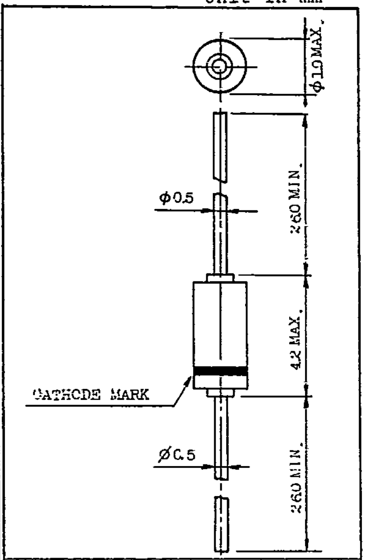
Diode

GENERAL PURPOSE APPLICATION FOR DETECTOR AND RECTIFIER.

FEATURES:

- Low Forward Voltage : V_F=1.0V (Typ.)
- Small Total Capacitance : C_T=1.3pF (Typ.)

Unit in mm



JEDEC	DO-35
EIAJ	SC-40
TOSHIBA	1-2A1A

Weight : 0.14g

Marking

1S1553

1S1554

1S1555

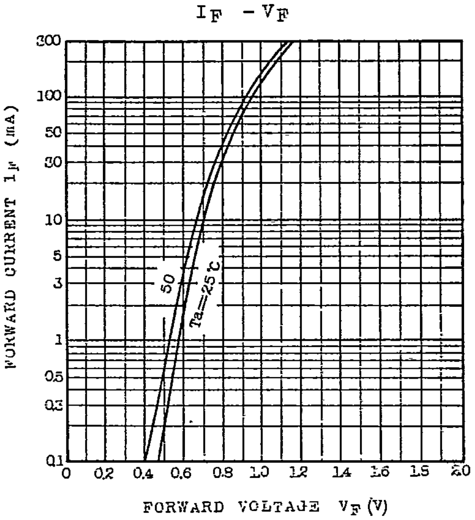
MAXIMUM RATINGS (Ta=25°C)

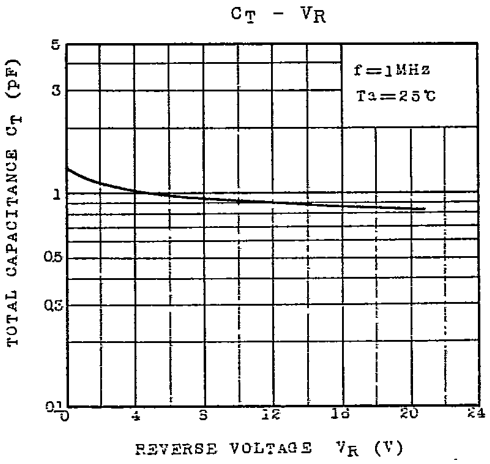
CHARACTERISTIC		SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	1S1553	V_{RM}	70	V
	1S1554		55	
	1S1555		35	
Reverse Voltage	1S1553	V_R	60	V
	1S1554		50	
	1S1555		30	
Maximum (Peak) Forward Current		I_{FM}	300	mA
Average Forward Current		I_O	100	mA
Surge Current (1 sec)		I_{FSM}	1	A
Power Dissipation		P	300	mW
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	-65~150	°C

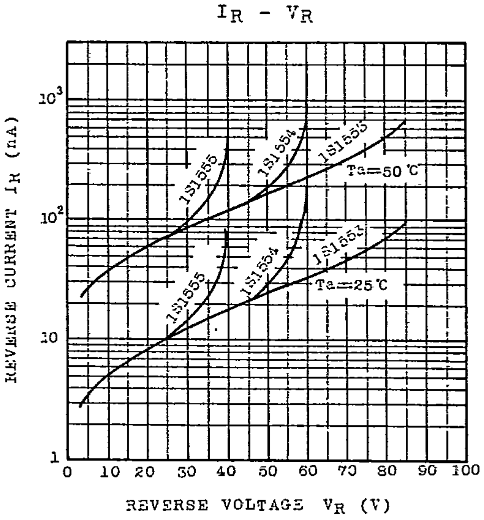
ELECTRICAL CHARACTERISTICS (Ta=25°C)

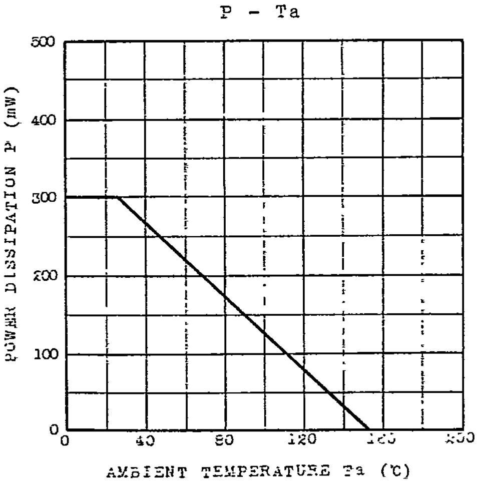
CARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage		V_F	I_F=100mA	-	1.0	1.4	V
Reverse Current	1S1553	I_R	V_R=60V	-	-	0.5	μA
	1S1554		V_R=50V				
	1S1555		V_R=30V				
Total Capacitance		C_T	V_R=0 f=1MHz	-	1.3	3.5	pF

1S1553~1S1555


IF - VF


CT - VR


IR - VR


P - Ta